2SC5124

Silicon NPN Triple Diffused Planar Transistor (High Voltage Switchihg Transistor)

Application : Display Horizontal Deflection Output, Switching Regulator and General Purpose

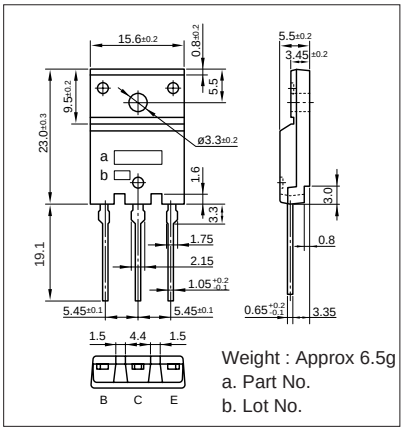
■Absolute maximum ratings (Ta=25°C)

Symbol	Ratings	Unit
V_{CBO}	1500	V
V_{CEO}	800	V
V_{EBO}	6	V
I_C	10(Pulse20)	A
I_B	5	A
P_C	100(Tc=25°C)	W
Tj	150	°C
Tstg	–55 to +150	°C

■Electrical Characteristics (Ta=25°C)

Symbol	Conditions	Ratings	Unit
I_{CBO1}	V_{CB}=1200V	100max	μA
I_{CBO2}	V_{CB}=1500V	1max	mA
I_{EBO}	V_{EB}=6V	100max	μA
$V_{(BR)CEO}$	I_C=10mA	800min	V
h_{FE1}	V_{CE}=5V, I_C=1A	8min	
h_{FE2}	V_{CE}=5V, I_C=8A	4to9	
V_{CE}(sat)	I_C=8A, I_B=2A	5max	V
V_{BE}(sat)	I_C=8A, I_B=2A	1.5max	V
f_T	V_{CE}=12V, I_E=–1A	3typ	MHz
C_{OB}	V_{CB}=10V, f=1MHz	130typ	pF

External Dimensions FM100(TO3PF)

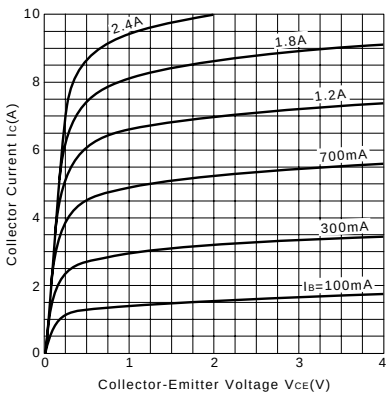


Weight : Approx 6.5g
a. Part No.
b. Lot No.

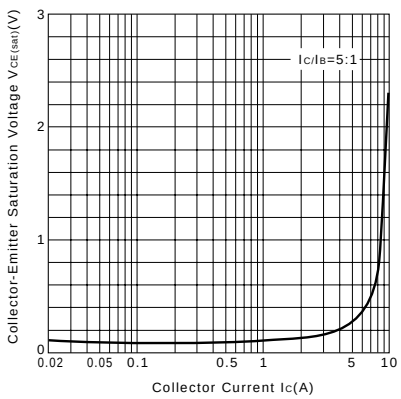
■Typical Switching Characteristics (Common Emitter)

V_{CC} (V)	R_L (Ω)	I_C (A)	V_{BB1} (V)	V_{BB2} (V)	I_{B1} (A)	I_{B2} (A)	ton (μs)	tstg (μs)	tf (μs)
200	33.3	6	10	–5	1.2	–2.4	0.1typ	4.0typ	0.2typ

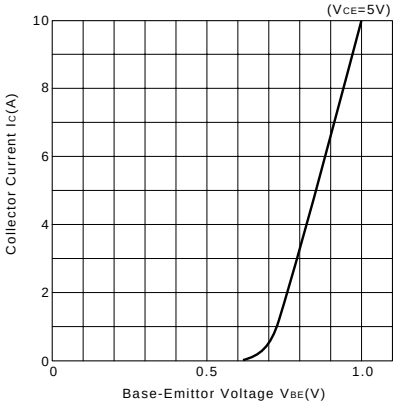
I_C–V_{CE} Characteristics (Typical)



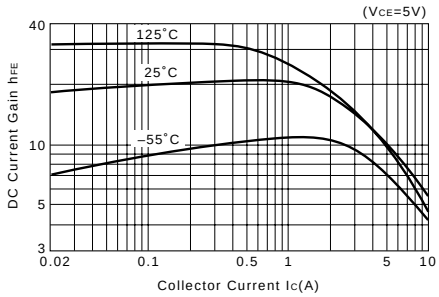
V_{CE}(sat)–I_C Characteristics (Typical)



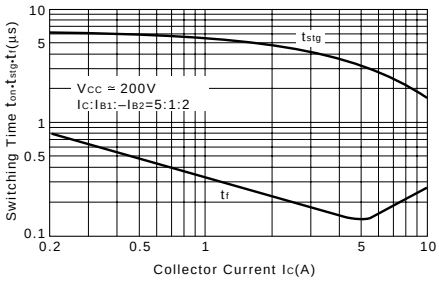
I_C–V_{BE} Temperature Characteristics (Typical)



h_{FE}–I_C Characteristics (Typical)

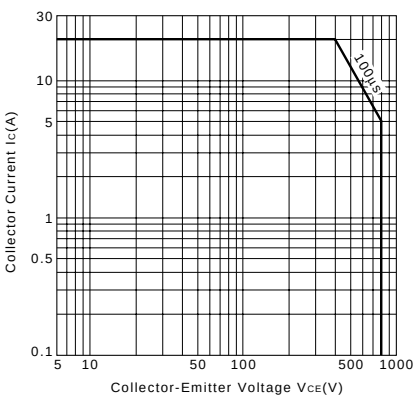


t_{stg}•t_f–I_C Characteristics (Typical)

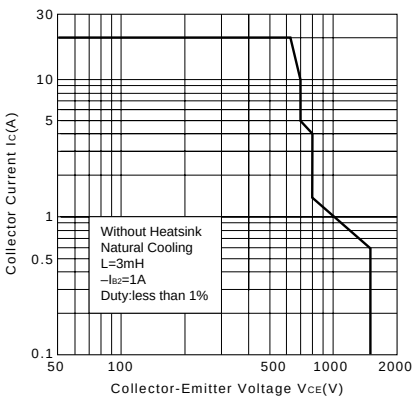


$\theta_{j\text{-}a}$–t Characteristics

Safe Operating Area (Single Pulse)



Reverse Bias Safe Operating Area



Pc–Ta Derating